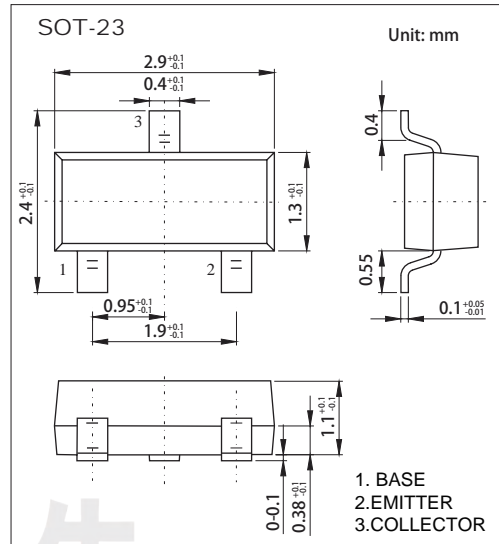


NPN Transistors 2SC1815

■ Features

- Excellent hFE Linearity
- Low noise
- Complementary to 2SA1015



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	60	V
Collector - Emitter Voltage	V _{CE0}	50	
Emitter - Base Voltage	V _{EB0}	5	
Collector Current - Continuous	I _c	150	mA
Collector Power Dissipation	P _c	200	mW
Thermal Resistance From Junction To Ambient	R _{θJA}	625	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	

NPN Transistors 2SC1815

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = 100 μA, I _E =0	60			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = 0.1 mA, I _B =0	50			
Emitter - base breakdown voltage	V _{EB0}	I _E = 100 μA, I _C =0	5			
Collector cut-off current	I _{CBO}	V _{CB} = 60 V, I _E =0			0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} = 50 V, I _B =0			0.1	
Emitter cut-off current	I _{EBO}	V _{EB} = 5V, I _C =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100 mA, I _B = 10mA			0.25	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =100 mA, I _B = 10mA			1	
DC current gain	h _{FE}	V _{CE} = 6V, I _C = 2mA	130		400	
Transition frequency	f _T	V _{CE} = 10V, I _C = 1mA, f=30MHz	80			MHz

■ Classification of h_{FE}

Rank	L	H
Range	130-200	200-400
Marking	HF	

Transistor

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Typical Characteristics

